

74F827

10-bit buffer/line driver; non-inverting; 3-state

Rev. 04 — 29 January 2010

Product data sheet

1. General description

The 74F827 10-bit buffer, provides high performance bus interface buffering for wide data/address paths or buses carrying parity. The device has NOR output enables ($\overline{OE}0$, $\overline{OE}1$) for maximum control flexibility.

2. Features

- High impedance NPN base inputs for reduced loading (20 μ A input current in HIGH and LOW states)
- $I_{IL} = 20 \mu\text{A}$ compared to 600 μA in FAST family specification
- Ideal for high speed, light bus loading with increased fan-in
- Controlled rise and fall times to minimize ground bounce
- Glitch-free power-up in 3-state
- Flow-through pinout architecture for microprocessor oriented applications
- Output sink capability, $I_{OL} = 64 \text{ mA}$

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
N74F827D	0 °C to 70 °C	SO24	plastic small outline package; 24 leads; body width 7.5 mm	SOT137-1
N74F827DB	0 °C to 70 °C	SSOP24	plastic shrink small outline package; 24 leads; body width 5.3 mm	SOT340-1

4. Functional diagram

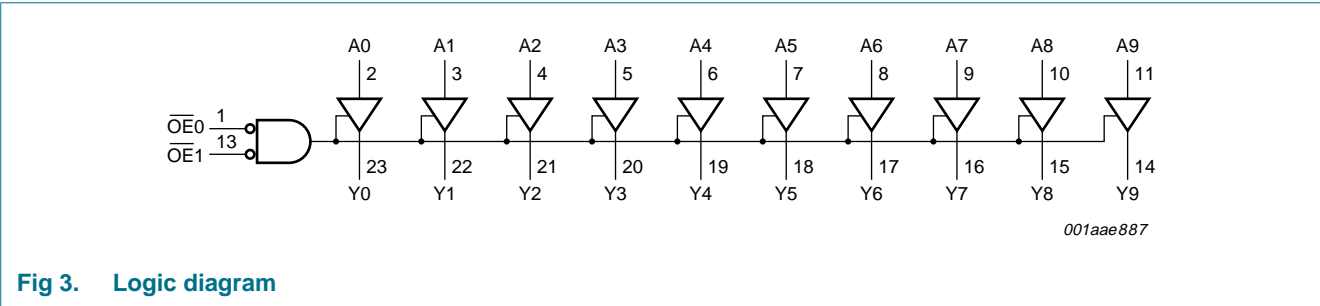
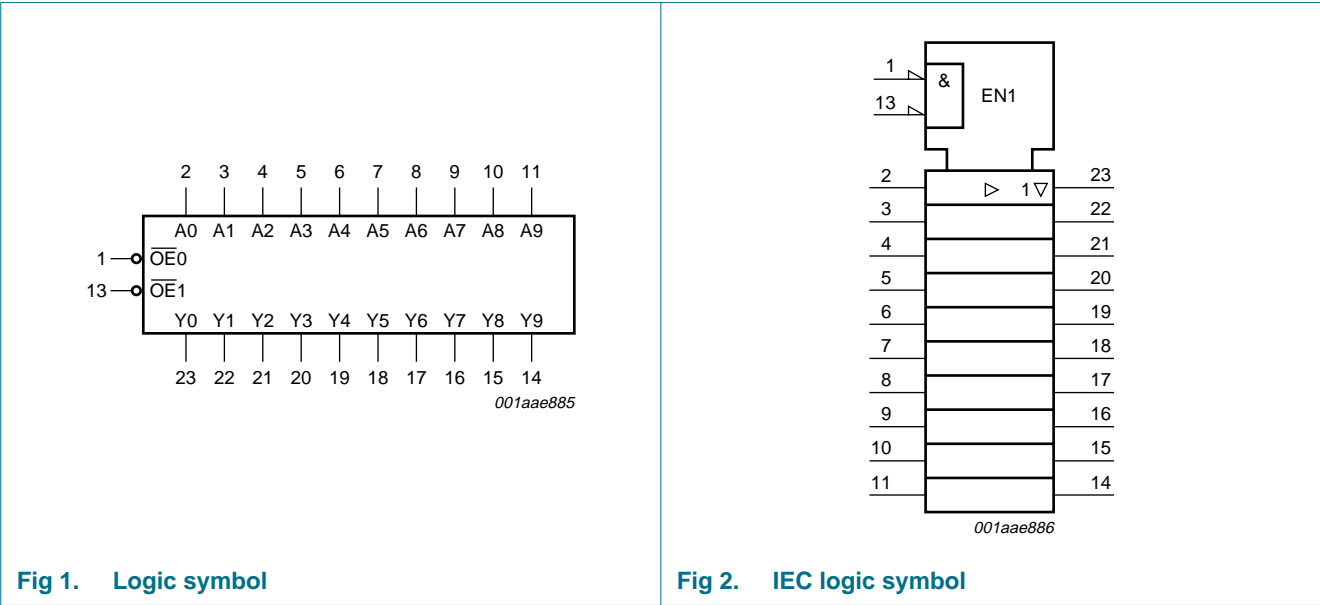


Fig 3. Logic diagram

5. Pinning information

5.1 Pinning

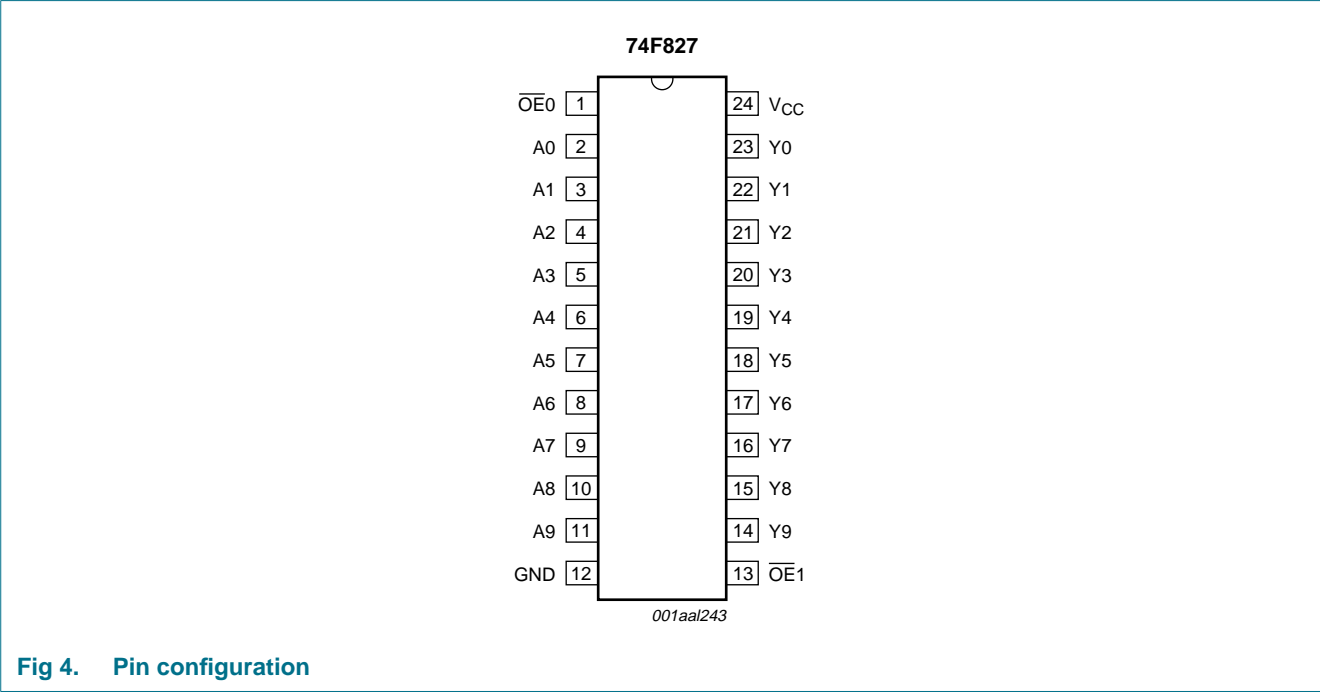


Fig 4. Pin configuration

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description	Unit load HIGH/LOW	Load value ^[1] HIGH/LOW
OE0	1	output enable input (active LOW)	1.0/0.033	20 µA/20 µA
A0 to A9	2, 3, 4, 5, 6, 7, 8, 9, 10, 11	data input	1.0/0.033	20 µA/20 µA
GND	12	ground (0 V)	-	-
OE1	13	output enable input (active LOW)	1.0/0.033	20 µA/20 µA
Y0 to Y9	23, 22, 21, 20, 19, 18, 17, 16, 15, 14	data output	1200/106.7	24 mA/64 mA
VCC	24	supply voltage	-	-

[1] One FAST Unit Load (UL) is defined as 20 µA in HIGH state, 0.6 µA in LOW state.

6. Functional description

6.1 Function table

Table 3. Function selection^[1]

Input		Output	Status
OEn	An	Yn	
L	L	L	transparent
L	H	H	
H	X	Z	disabled

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care;
 Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
V _I	input voltage		^[1] -0.5	+7.0	V
V _O	output voltage	output in HIGH-state	^[1] -0.5	+7.0	V
I _{IK}	input clamping current	V _I < 0 V	-30	+5	mA
I _O	output current	output in LOW-state	-	128	mA
T _{amb}	ambient temperature	in free-air	^[2] 0	70	°C
T _{stg}	storage temperature		-65	+150	°C

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 [2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage		4.5	5.0	5.5	V
V _{IH}	HIGH-level input voltage		2.0	-	-	V
V _{IL}	LOW-level input voltage		-	-	0.8	V
I _{IK}	input clamping current		-18	-	-	mA
I _{OH}	HIGH-level output current		-24	-	-	mA
I _{OL}	LOW-level output current		-	-	64	mA

9. Static characteristics

Table 6. Static characteristics

Symbol	Parameter	Conditions	25 °C			0 °C to 70 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{IK}	input clamping voltage	V _{CC} = 4.5 V; I _{IK} = -18 mA	-1.2	-0.73	-	-1.2	-	V
V _{OH}	HIGH-level output voltage	V _{CC} = 4.5 V; V _{IL} = 0.8 V; V _{IH} = 2.0 V						
		I _{OH} = -15 mA						
		V _{CC} = ±10 %	-	-	-	2.4	-	V
		V _{CC} = ±5 %	-	3.3	-	2.4	-	V
		I _{OH} = -24 mA						
		V _{CC} = ±10 %	-	-	-	2.0	-	V
V _{OL}	LOW-level output voltage	V _{CC} = 4.5 V; V _{IL} = 0.8 V; V _{IH} = 2.0 V						
		I _{OL} = 64 mA						
		V _{CC} = ±10 %	-	-	-	-	0.55	V
		V _{CC} = ±5 %	-	0.42	-	-	0.55	V
I _I	input leakage current	V _{CC} = 0 V; V _I = 7.0 V	-	-	-	-	100	μA
I _{IH}	HIGH-level input current	V _{CC} = 5.5 V; V _I = 2.7 V	-	-	-	-	20	μA
I _{IL}	LOW-level input current	V _{CC} = 5.5 V; V _I = 0.5 V	-	-	-	-	-20	μA
I _{OZ}	OFF-state output current	V _{CC} = 5.5 V						
		V _O = 2.7 V	-	-	-	-	50	μA
		V _O = 0.5 V	-	-	-	-	-50	μA
I _O	output current	V _{CC} = 5.5 V ^[2]	-	-	-	-100	-225	mA
I _{CC}	supply current	V _{CC} = 5.5 V; V _I = GND or V _{CC}						
		outputs HIGH-state	-	50	-	-	70	mA
		outputs LOW-state	-	70	-	-	100	mA
		outputs OFF-state	-	60	-	-	90	mA

[1] All typical values are measured at V_{CC} = 5 V.

[2] Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

10. Dynamic characteristics

Table 7. Dynamic characteristics

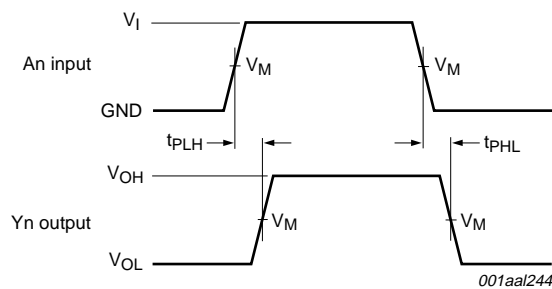
GND = 0 V; for test circuit, see [Figure 7](#).

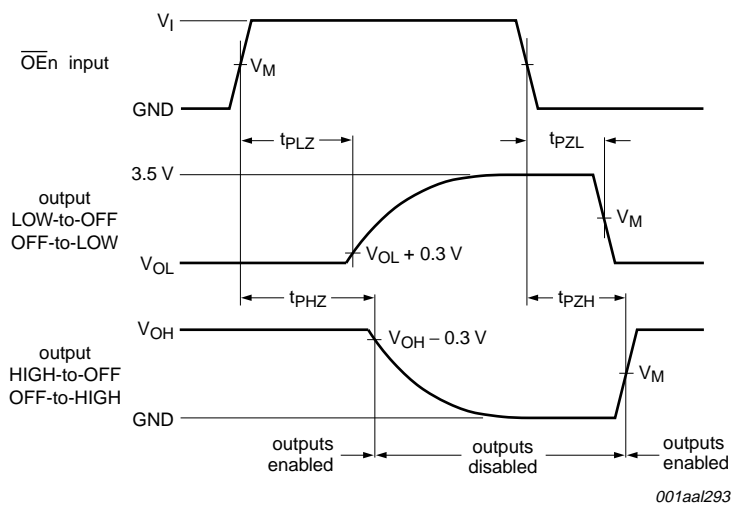
Symbol	Parameter	Conditions	25 °C; V _{CC} = 5.0 V			0 °C to 70 °C; V _{CC} = 5.0 V ± 0.5 V		Unit
			Min	Typ	Max	Min	Max	
t _{PLH}	LOW to HIGH propagation delay	An to Yn; see Figure 5						
		C _L = 50 pF	2.0	5.5	8.5	2.0	9.0	ns
		C _L = 300 pF, 1 output switching	-	9.5	13.0	-	14.0	ns
		C _L = 300 pF, 10 outputs switching	-	12.0	16.0	-	17.0	ns

Table 7. Dynamic characteristics ...continuedGND = 0 V; for test circuit, see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C; V _{CC} = 5.0 V			0 °C to 70 °C; V _{CC} = 5.0 V ± 0.5 V		Unit
			Min	Typ	Max	Min	Max	
t _{PHL}	HIGH to LOW propagation delay	An to Yn; see Figure 5						
		C _L = 50 pF	2.0	4.5	8.5	2.0	9.0	ns
		C _L = 300 pF, 1 output switching	-	7.5	10.0	-	11.0	ns
		C _L = 300 pF, 10 outputs switching	-	14.0	17.0	-	18.0	ns
t _{PZH}	OFF-state to HIGH propagation delay	$\overline{\text{OEn}}$ to Yn; see Figure 6						
		C _L = 50 pF	5.0	8.0	12.0	4.5	14.0	ns
		C _L = 300 pF, 1 output switching	-	15.0	20.0	-	21.0	ns
		C _L = 300 pF, 10 outputs switching	-	15.0	20.0	-	21.0	ns
t _{PZL}	OFF-state to LOW propagation delay	$\overline{\text{OEn}}$ to Yn; see Figure 6						
		C _L = 50 pF	4.0	6.0	10.5	4.0	11.5	ns
		C _L = 300 pF, 1 output switching	-	9.5	13.0	-	14.0	ns
		C _L = 300 pF, 10 outputs switching	-	17.0	21.0	-	21.5	ns
t _{PHZ}	HIGH to OFF-state propagation delay	$\overline{\text{OEn}}$ to Yn; see Figure 6						
		C _L = 50 pF	2.5	5.0	8.0	2.0	8.5	ns
		C _L = 300 pF, 1 output switching	-	15.0	19.0	-	20.0	ns
		C _L = 300 pF, 10 outputs switching	-	15.0	19.0	-	20.0	ns
t _{PLZ}	LOW to OFF-state propagation delay	$\overline{\text{OEn}}$ to Yn; see Figure 6						
		C _L = 50 pF	2.5	5.0	8.0	2.0	8.5	ns
		C _L = 300 pF, 1 output switching	-	9.5	13.5	-	14.0	ns
		C _L = 300 pF, 10 outputs switching	-	12.5	15.5	-	16.0	ns

11. Waveforms

V_M = 1.5 VV_{OL} and V_{OH} are typical voltage output levels that occur with the output load.**Fig 5. Propagation delay input (An) to output (Yn)**



$V_M = 1.5\text{ V}$
 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. Propagation delay 3-state output enable time to LOW-level and output disable time from LOW-level

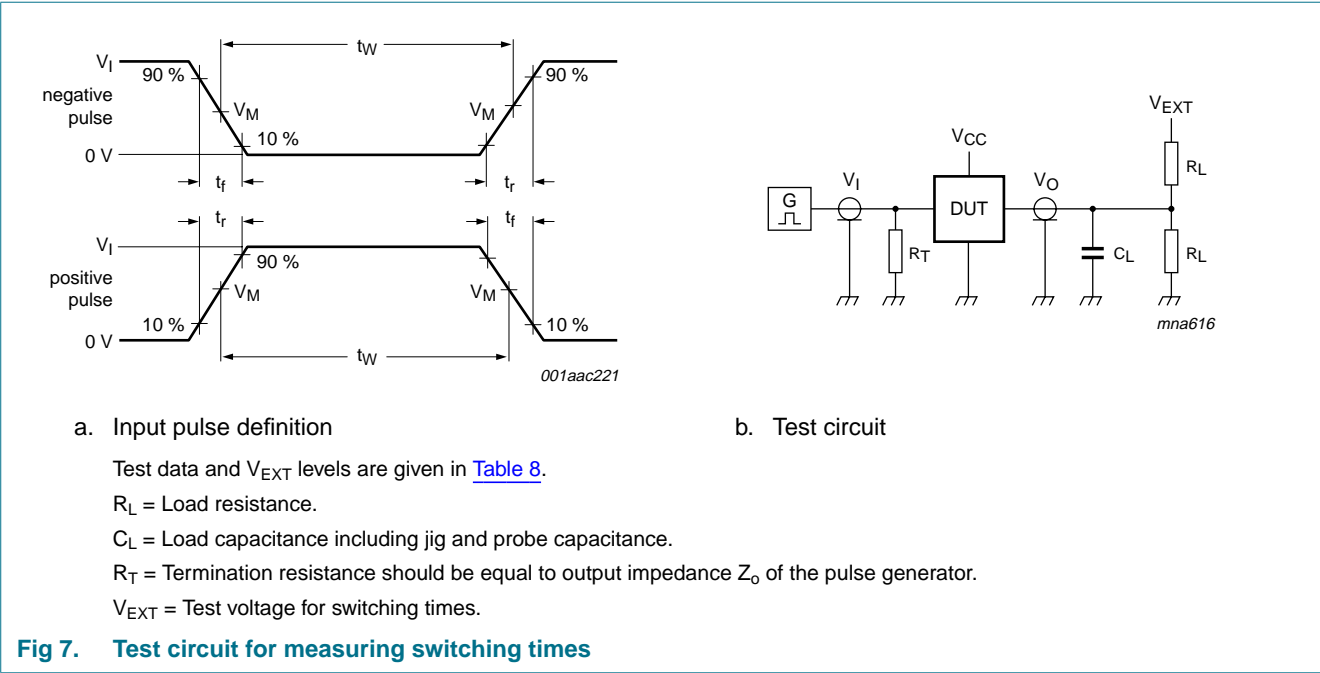


Fig 7. Test circuit for measuring switching times

Table 8. Test data

Input				Load		V_{EXT}		
V_I	f_I	t_W	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
3.0 V	1 MHz	500 ns	≤ 2.5 ns	50 pF	500 Ω	open	open	7.0 V

12. Package outline

SO24: plastic small outline package; 24 leads; body width 7.5 mm

SOT137-1

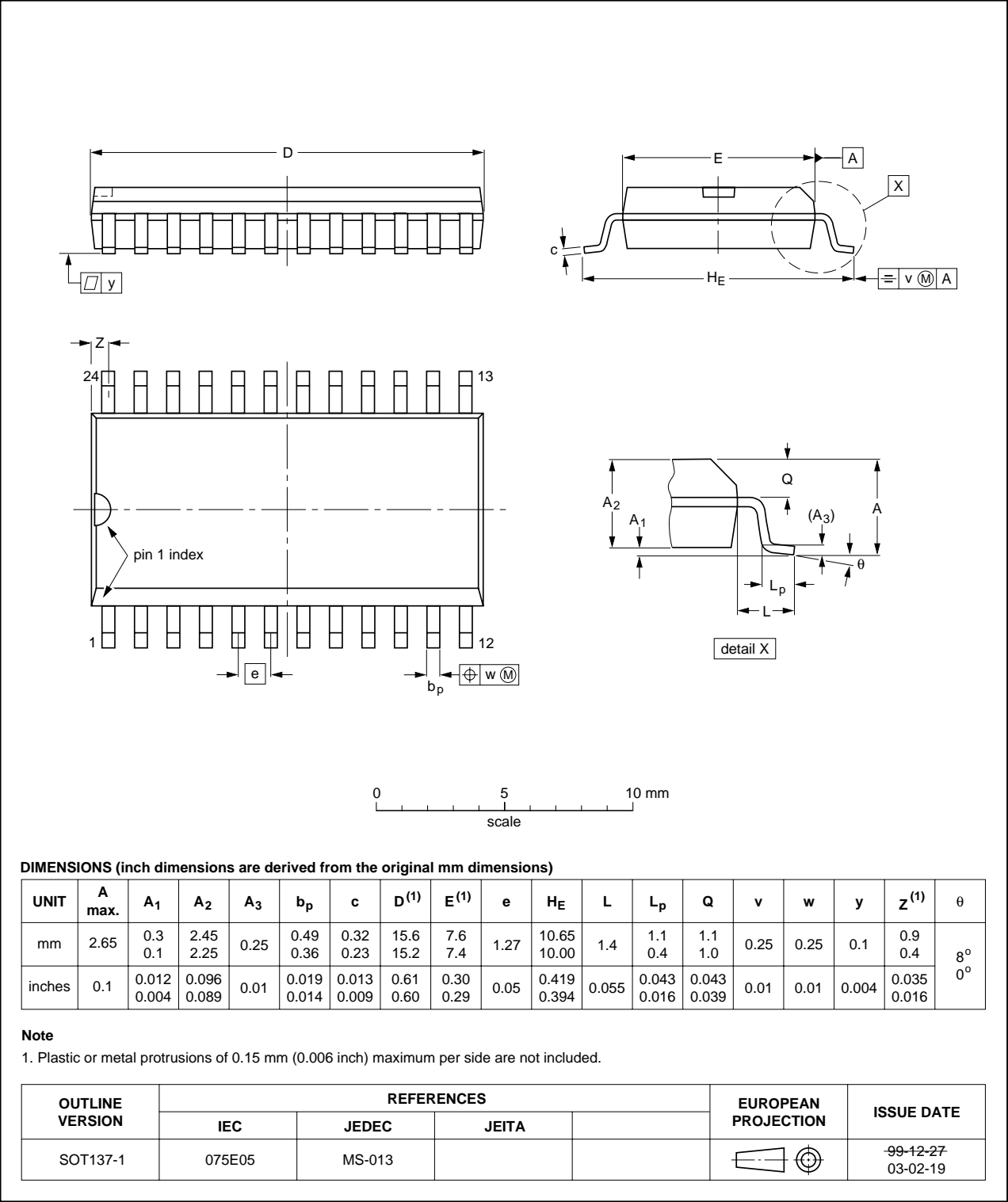


Fig 8. Package outline SOT137-1 (SO24)

SSOP24: plastic shrink small outline package; 24 leads; body width 5.3 mm

SOT340-1

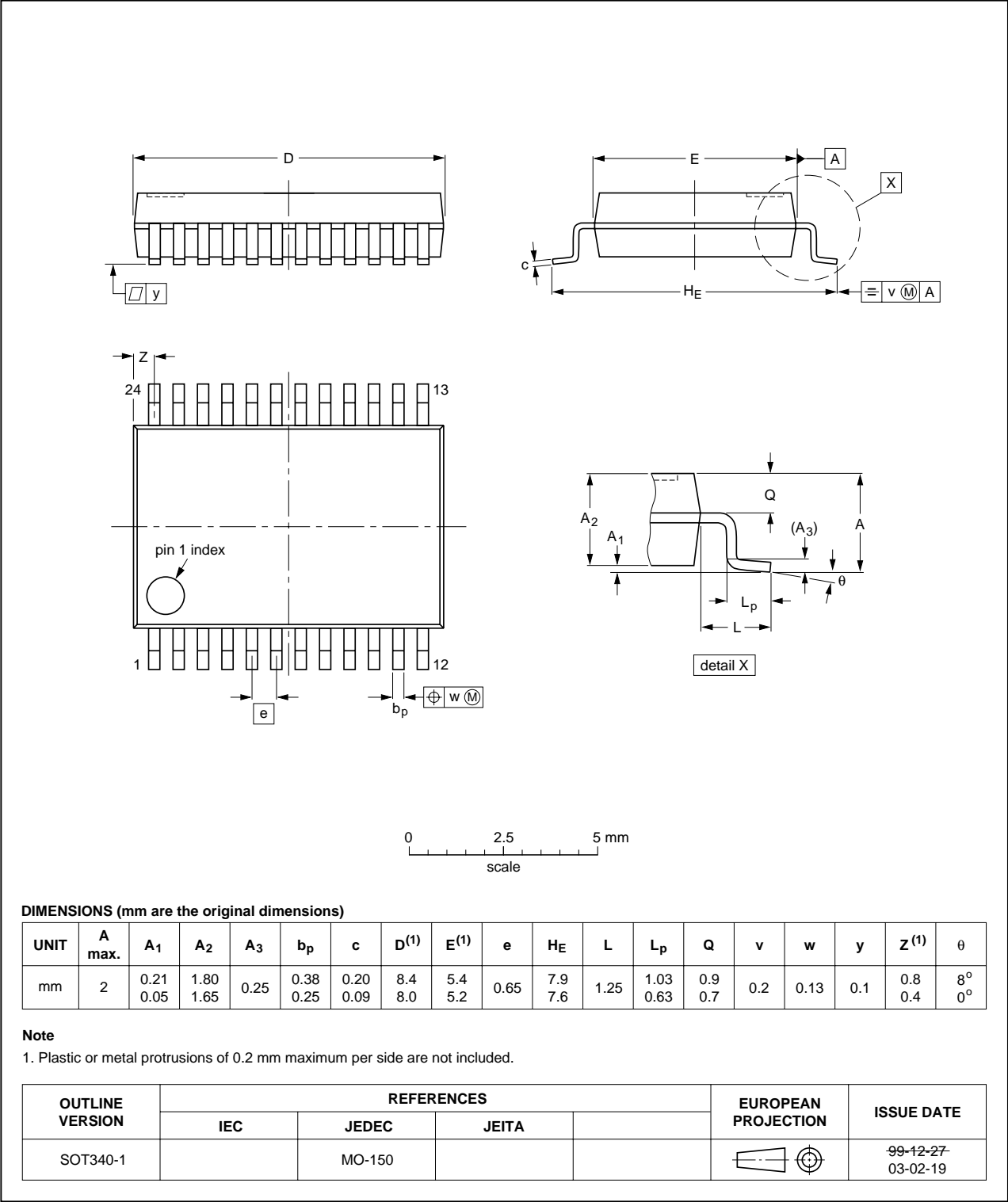


Fig 9. Package outline SOT340-1 (SSOP24)

13. Abbreviations

Table 9. Abbreviations

Acronym	Description
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

14. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74F827_4	20100129	Product data sheet	-	74F827_3
Modifications:	<ul style="list-style-type: none">• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.• Legal texts have been adapted to the new company name where appropriate.• DIP 24 (SOT222-1) package removed from Section 3 “Ordering information” and Section 12 “Package outline”			
74F827_3	20040121	Product specification	-	74F827_74F828_2
74F827_74F828_2	19941205	Product specification	-	-

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15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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